

FIG.1

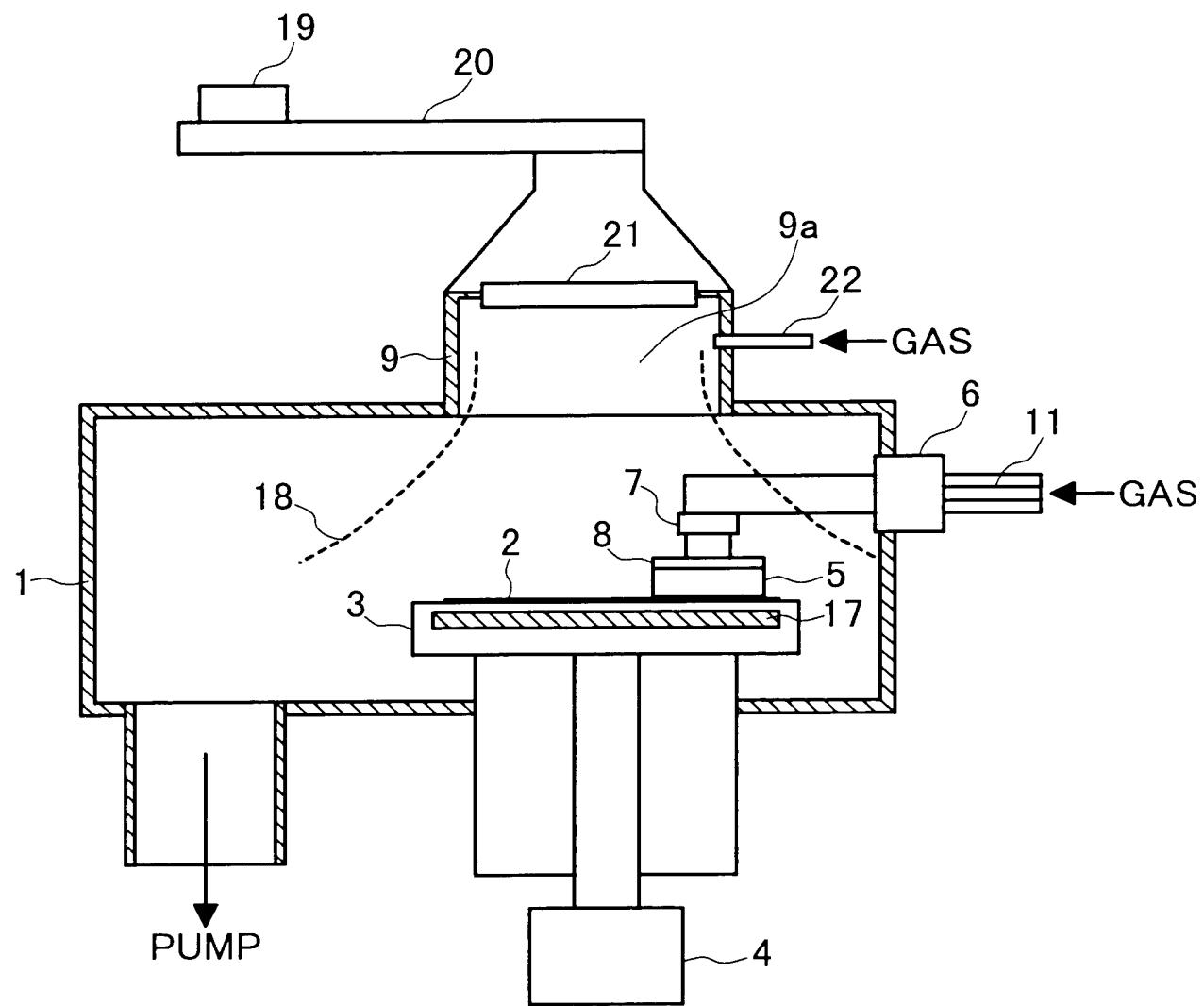


FIG.2

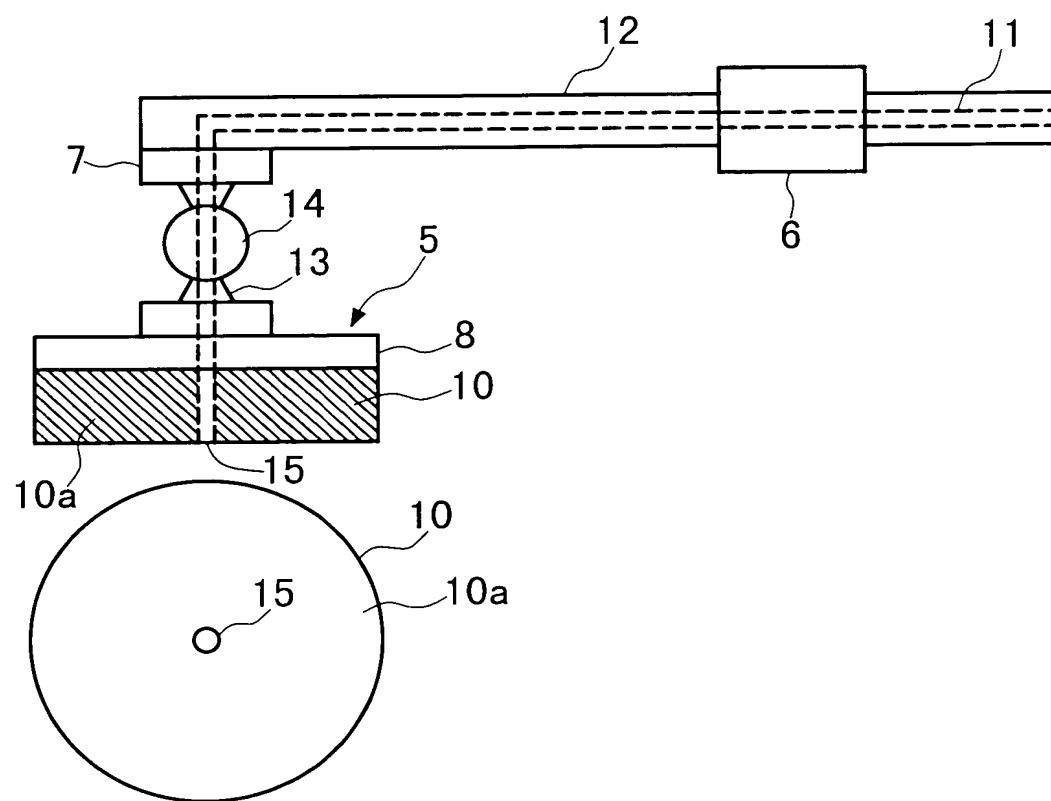


FIG.3

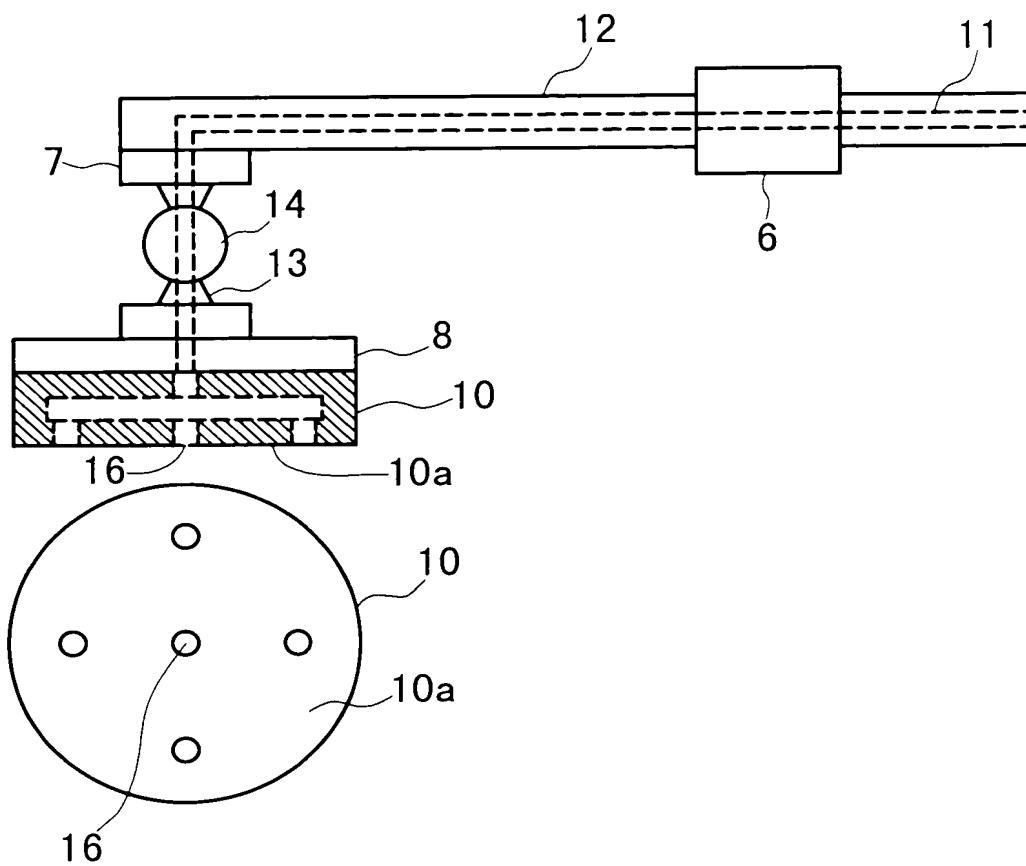


FIG.4

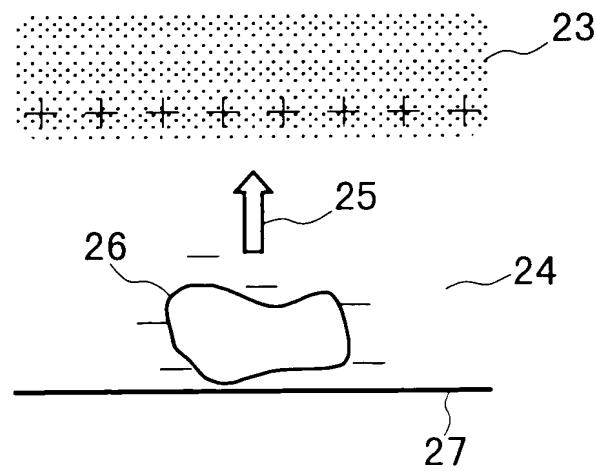


FIG.5

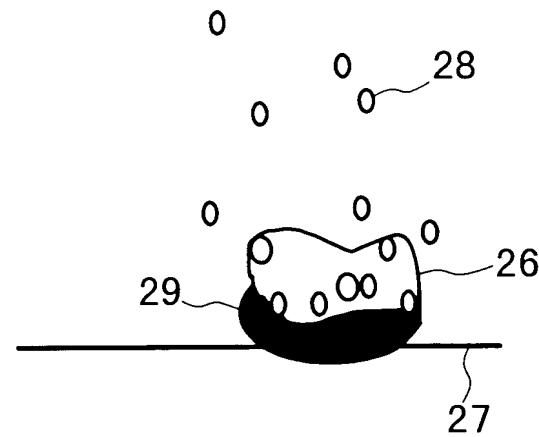


FIG.6

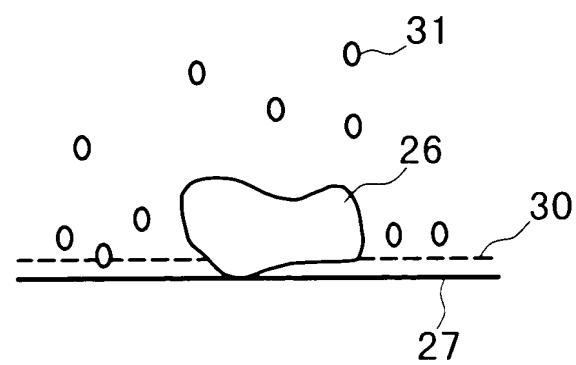


FIG.7

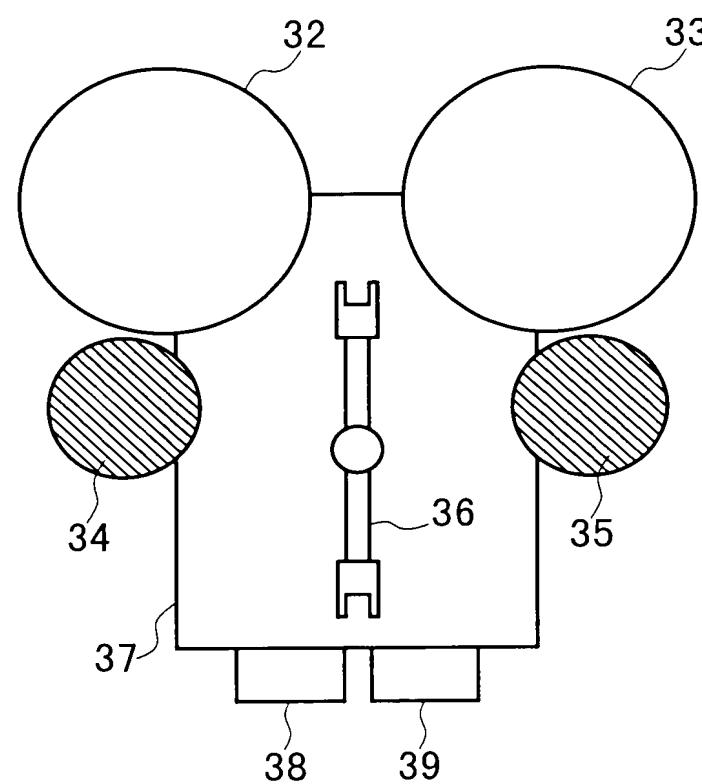


FIG.8

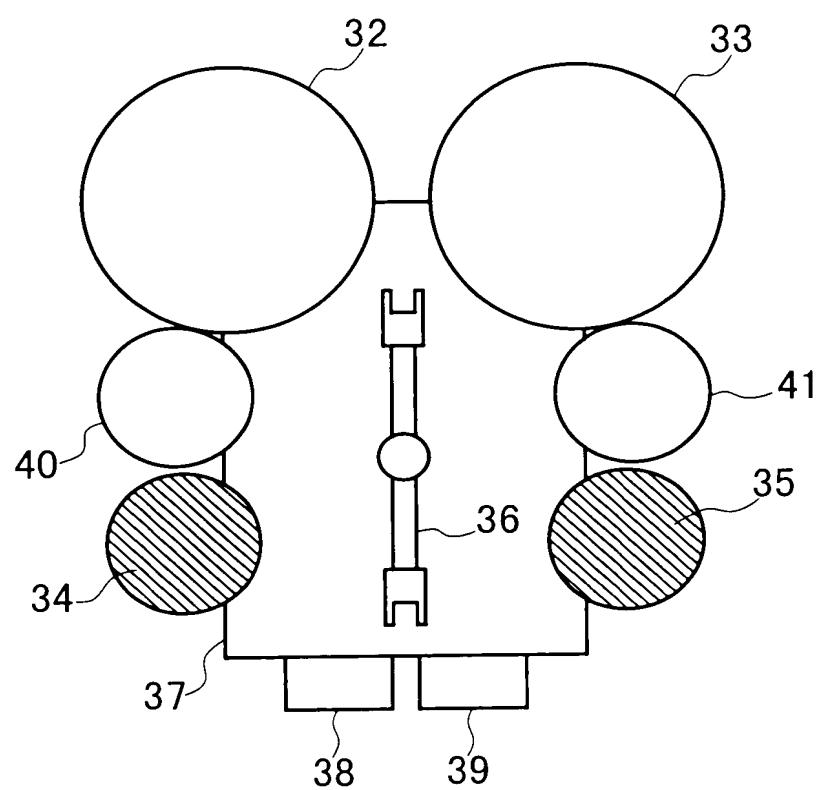


FIG.9

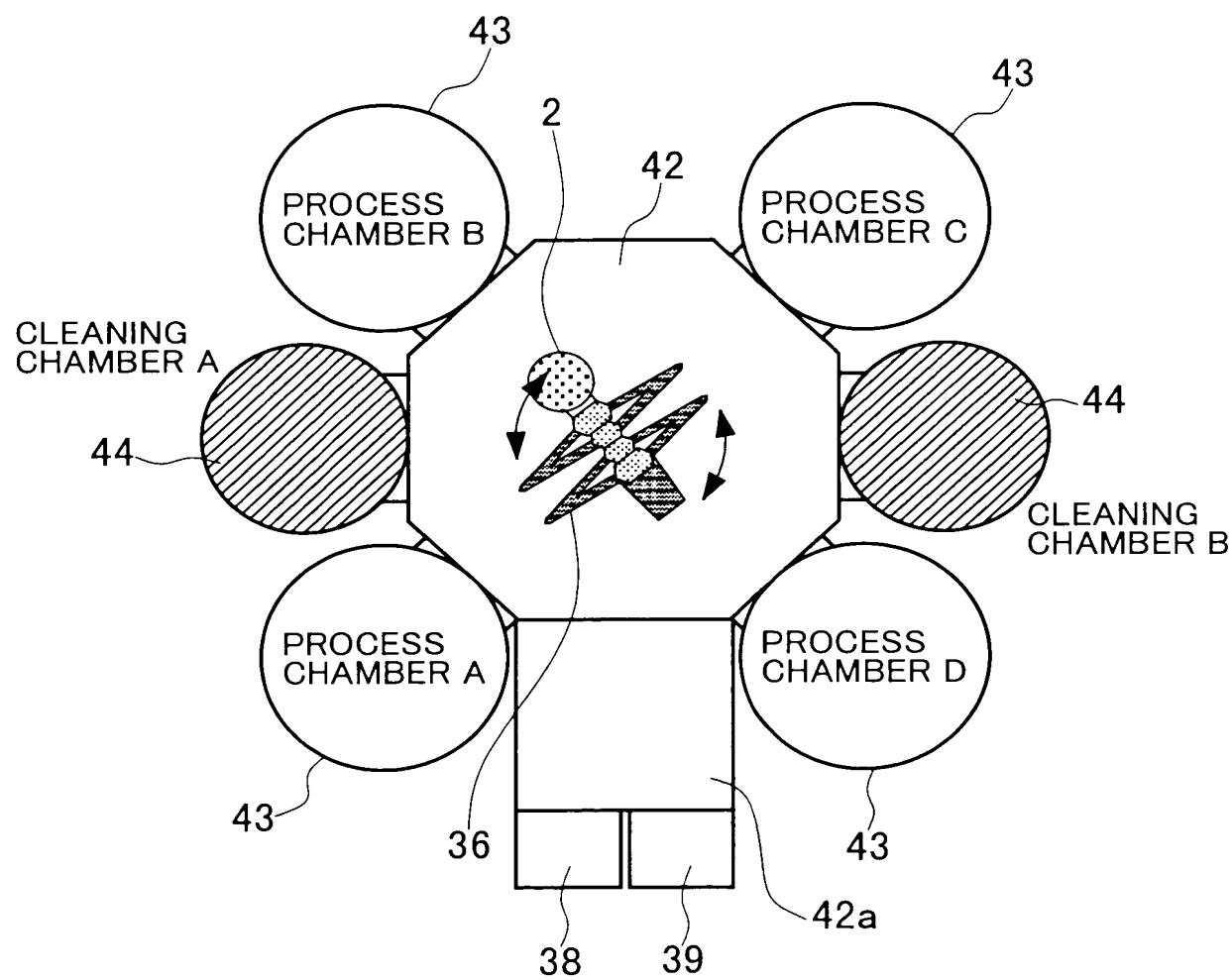


FIG.10A

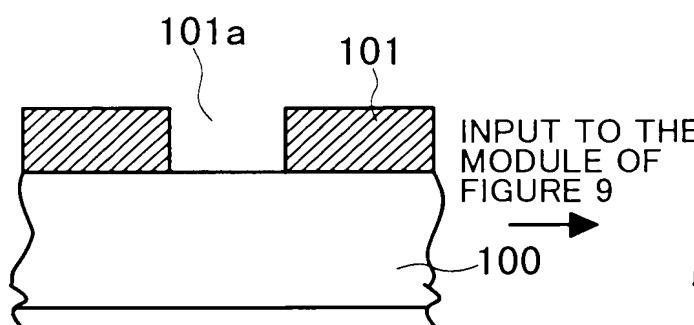


FIG.10B

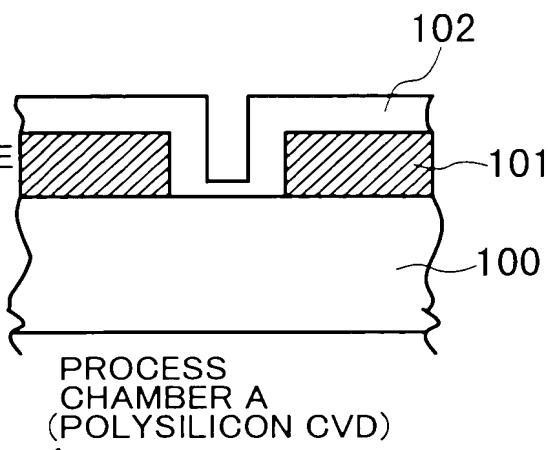


FIG.10C (CLEANING CHAMBER A)

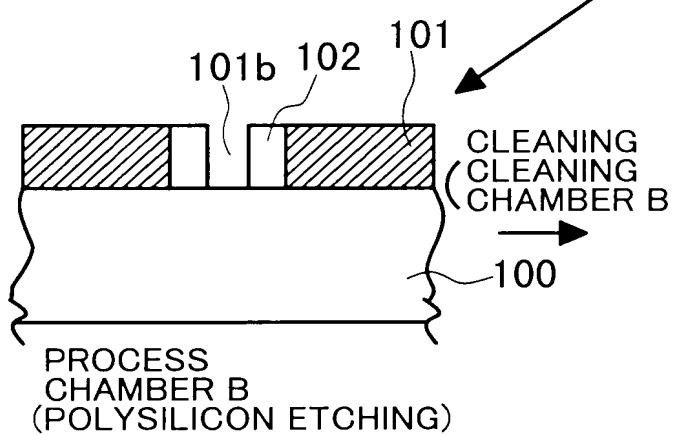


FIG.10D

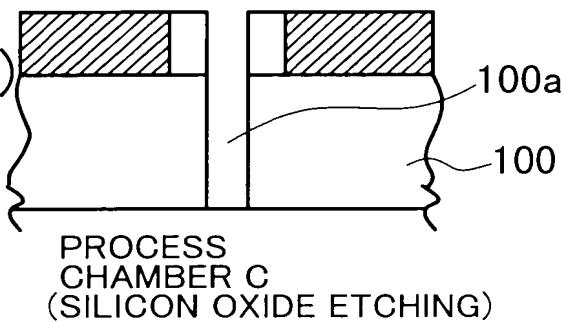


FIG.10E

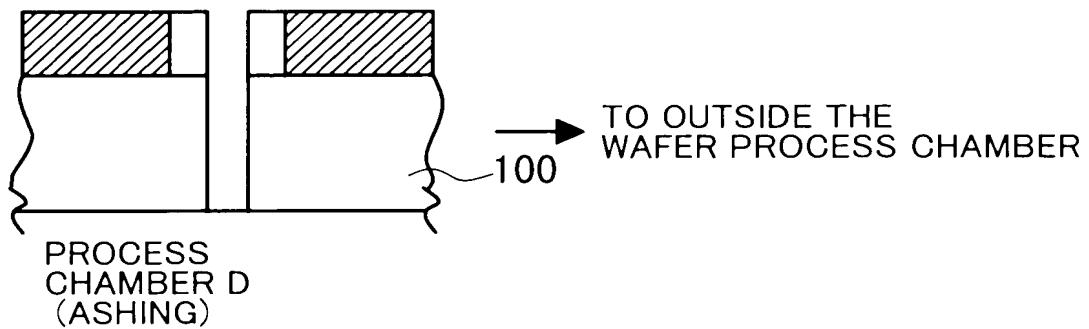
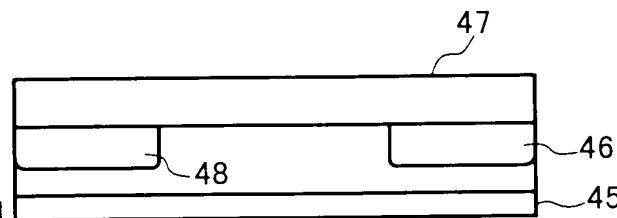
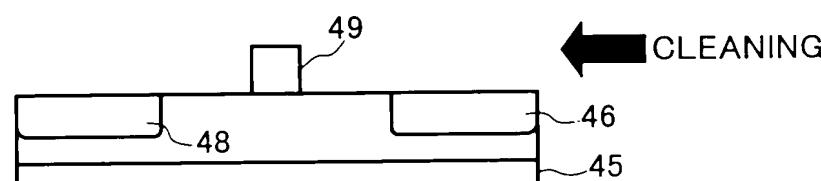


FIG.11A

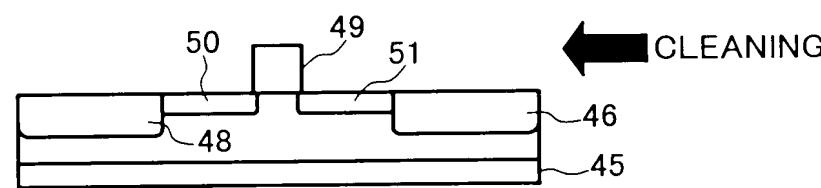
FABRICATION
OF DEVICE ISOLATION
REGION AND DEPOSITION
OF POLYSILICON

**FIG.11B**

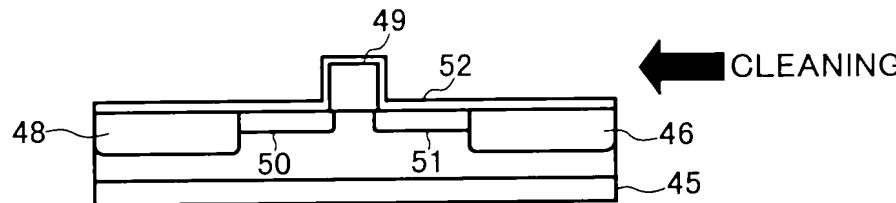
FABRICATION
OF GATE ELECTRODE
(POLYSILICON ETCHING)

**FIG.11C**

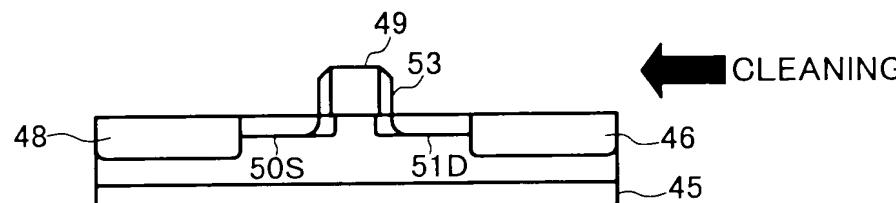
FABRICATION
OF EXTENSION

**FIG.11D**

DEPOSITION
OF NITRIDE FILM

**FIG.11E**

FABRICATION
OF GATE SIDE
WALL FILM

**FIG.11F**

FABRICATION
OF SILISIDE

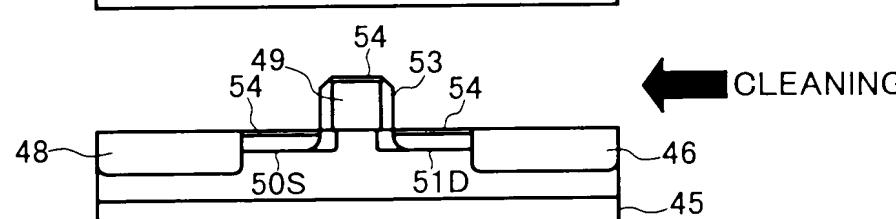


FIG.12A

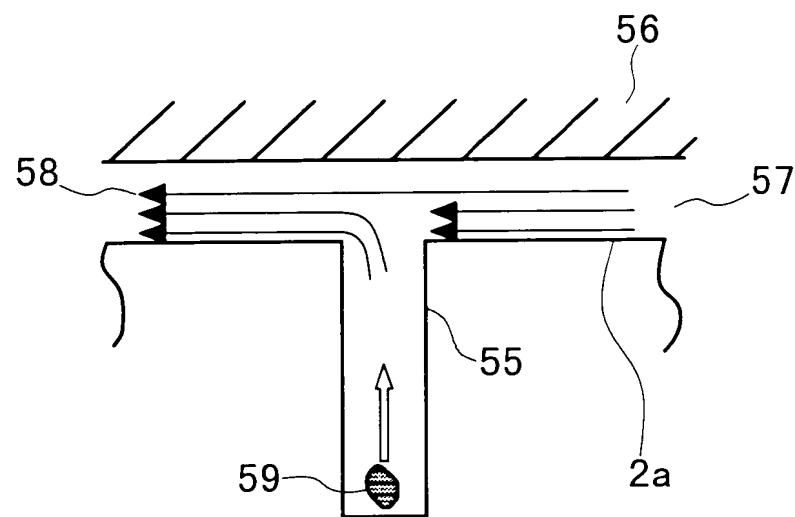


FIG.12B

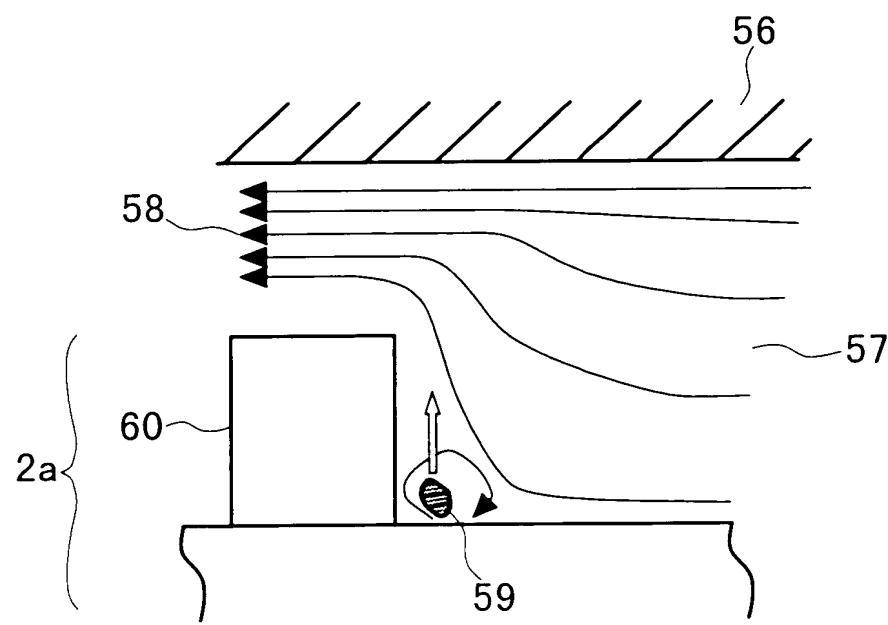


FIG.13

